

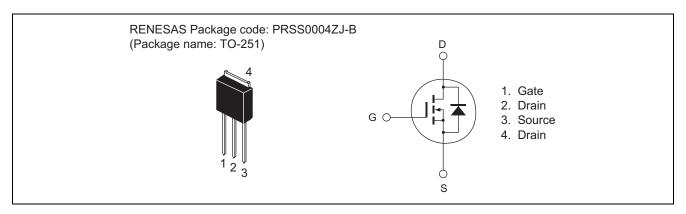
RJK6032DPH-E0

600V - 3A - MOS FET High Speed Power Switching R07DS0993EJ0100 Rev.1.00 Jan 23, 2013

Features

- Low on-resistance $R_{DS(on)}=3.3~\Omega~typ.~(at~I_D=1.0~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	3	А
Drain peak current	I _{D (pulse)} Note1	6	А
Body-drain diode reverse drain current	I _{DR}	3	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	6	Α
Avalanche current	I _{AP} Note2	3	Α
Avalanche energy	E _{AR} Note2	0.49	mJ
Channel dissipation	Pch Note3	40.3	W
Channel to case thermal impedance	θch-c	3.1	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,~duty~cycle \leq$ 1%

- 2. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 3. Value at Tc = 25°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

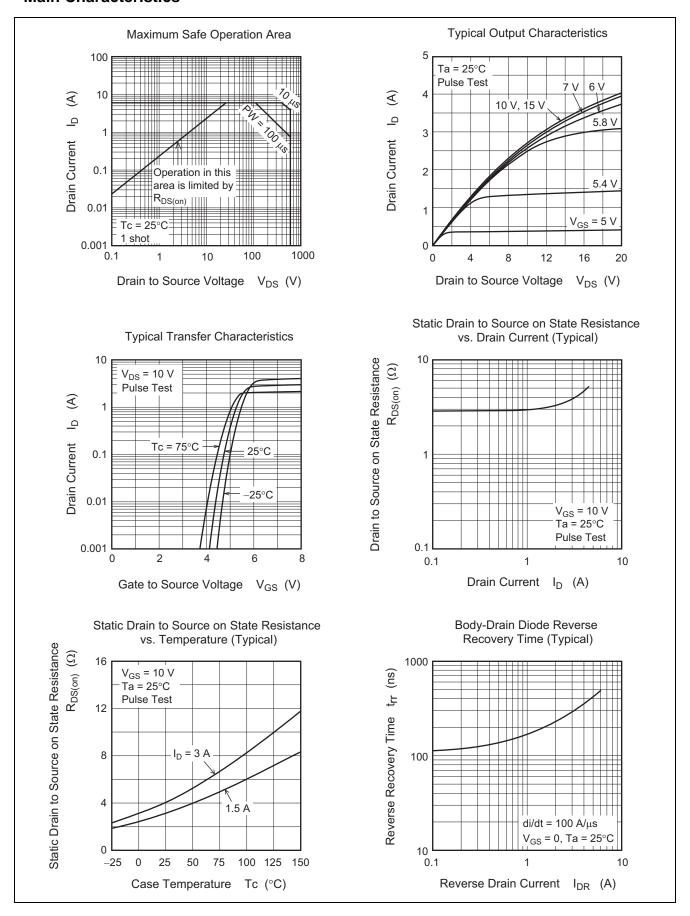
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}			1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	3.3	4.3	Ω	$I_D = 1.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss		285	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	31	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	3.5	_	pF	
Turn-on delay time	t _{d(on)}	_	13	_	ns	$I_D = 1.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 200 \Omega$ $Rg = 10 \Omega$
Rise time	t _r	_	13	_	ns	
Turn-off delay time	$t_{d(off)}$	_	22	_	ns	
Fall time	t _f	_	22	_	ns	
Total gate charge	Qg	_	9.0	_	nC	$V_{DD} = 480 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 3 \text{ A}$
Gate to source charge	Qgs	_	1.7	_	nC	
Gate to drain charge	Qgd	_	4.9	_	nC	
Body-drain diode forward voltage	V_{DF}	_	0.9	1.5	V	$I_F = 3 A$, $V_{GS} = 0$ Note4
Body-drain diode reverse recovery time	t _{rr}	_	300	_	ns	$I_F = 3 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

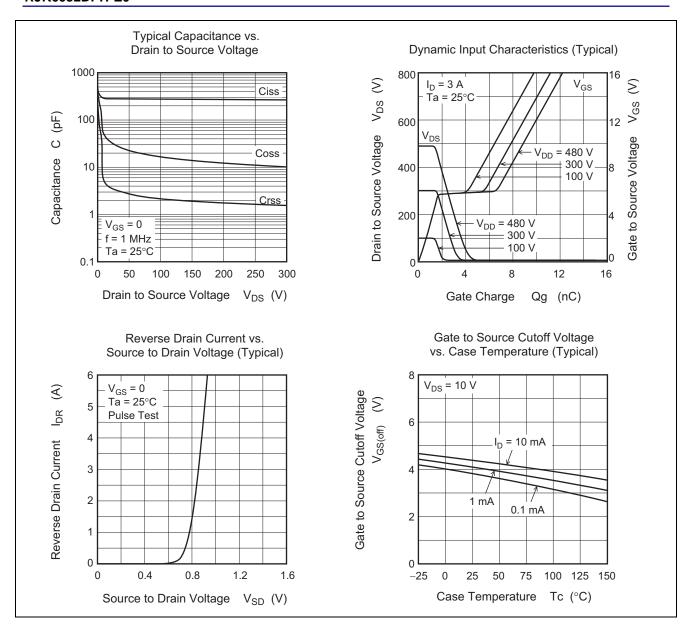
Notes: 4. Pulse test

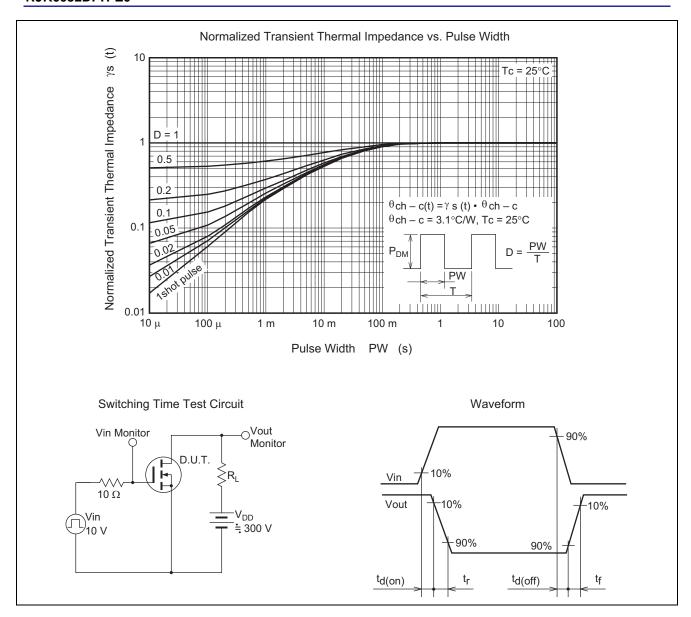
- 5. Since this device is equipped with high voltage FET chip ($V_{DSS} \ge 600 \text{ V}$), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.
- 6. This device is sensitive to electrostatic discharge.

 It is recommended to adopt appropriate cautions when handling this product.

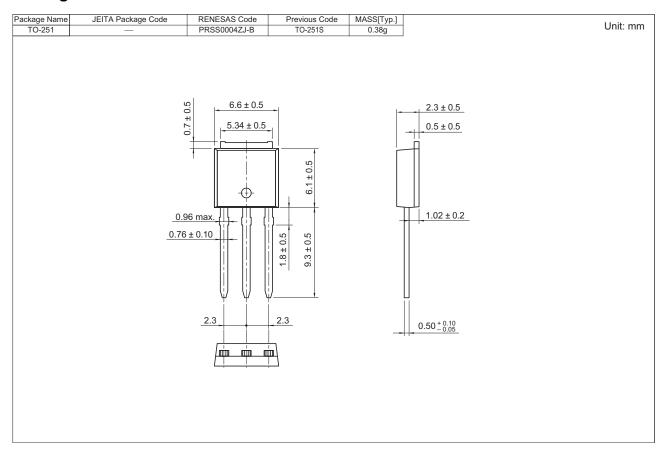
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK6032DPH-E0#T2	70 pcs	Tube

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Milliboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Ha Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 i. nunLu Haidian District. Beiiing 100083. P.R.China

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2868-9318, Fax: +852 2869-9022/9044

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949 Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2558-3737, Fax: 482-2558-5141

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